

Electronic Acknowledgement Receipt

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International Application Number:	
Confirmation Number:	2319
Title of Invention:	Stacked structure and production method thereof
First Named Inventor/Applicant Name:	Hubert Moriceau
Customer Number:	90678
Filer:	Jasper W. Dockrey
Filer Authorized By:	
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File Listing:

Document Number	Document Description	File Name	File Size(Bytes)/Message Digest	Multi Part/.zip	Pages (if appl.)
1	NPL Documents	Demeester_et_al_Epitaxial_Lift-Off_and_Its_Appns.pdf	1057147 e514a604e257a380e0cd7be60d17a95986a46b7c	no	13

Warnings:

Information:

2	NPL Documents	Denteneer_et_al_Hydrogen_Diffusion_and_Passivation_of_Shallow_Impurities.pdf	299205 0a8be7616264e456e107930a24c1956759a 6bbba	no	5
Warnings:					
Information:					
3	NPL Documents	Denteneer_et_al_Structure_and_Properties_of_Hydrogen-Impurity_Pairs.pdf	342276 a011f0edf7001ea0e4c4ca5f2627a3eef12 a0a	no	4
Warnings:					
Information:					
4	NPL Documents	DiCioccio_et_al_Silicon_Carbide_on_Insulator_Formation.pdf	130526 0f564e2811bb025e45d1755724c9b29800a 2a4	no	2
Warnings:					
Information:					
5	NPL Documents	Dirks_AG_et_al_Columnar_Microstructure_in_Vapor_Deposited_Thin_Films.pdf	1187199 6b699fb565b3cb5389aa3781ca71ec2b 786c9	no	15
Warnings:					
Information:					
6	NPL Documents	Duo_et-al_Comparison_Between_The_Different.pdf	821079 6519e4d26a98a6d32e8d5f09b517dca87 e6262	no	6
Warnings:					
Information:					
7	NPL Documents	Duo-et-al-Evolution-of-Hydrogen-and-Helium_1.PDF	549396 0e33f771a8074b5d56810798f3ca0f61f 281a	no	6
Warnings:					
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8	NPL Documents	Eaglesham_White_et_al_Equilibrium_Shape_of_Si.pdf	272298 56020e891fc127813254578fcf7de7e3d2 897b	no	4
Warnings:					
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9	NPL Documents	EerNisse_E-Compaction_of_Ion-Implanted_Fused_Silica.pdf	768866 8a0542aa6f4731b33857fcf6295c151ff17 1c2	no	8
Warnings:					
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10	NPL Documents	EerNisse_EP-Role_of_Integrated_Lateral_Stress_In_Surface_Deformation_of_He_Implanted_Surfaces.pdf	801341 1162516e6ad7556111b6a2253fb5cfcd4 1a70	no	9
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11	NPL Documents	Evans_JH_An_Interbubble_Fracture_Mechanism_Of_Blisters.pdf	869679 data:36616b716166b790ee19344ef6fe18ff6	no	12
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12	NPL Documents	Feijoo_et_al-Prestressing_of_Bonded.pdf	390788 data:56ab64f357ac020edf1121fd01b6e11644	no	9
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13	NPL Documents	Feng_et_al_Generalized_Formula_For_Curvature.pdf	137308 data:6967976311fe624statablefbfb51b2992515	no	3
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14	NPL Documents	Garner_DM-The_Fabrication_Of_A_Partial_SOI_Substrate.pdf	376649 data:65cd9647e91290398d1803fb2615e5024	no	6
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15	NPL Documents	Gerasimenko_N-Infrared_Absorption_of_Silicon_Irradiated_by_Phrons.pdf	423407 data:7b6bb377a6e9d753eab01e12fe12e42	no	7
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16	NPL Documents	Ghandi_Sorab-VSLI_Fabrication_Principles-Silicon_and_Gallium_Arsenide.pdf	145184 data:208786a79d146e8116d0901415e7917	no	4
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17	NPL Documents	Greenwald_AC-Pulsed-Electron-Beam_Annealing_of_Ion-Implantation_Damage.pdf	364299 data:ce2e759b237305663f333126af241e01aa	no	4
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18	NPL Documents	Grovenor_C_Microelectronic_Materials.pdf	183072 data:89cb2957b0411504f92e143630792099	no	5
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19	NPL Documents	Guilhalmenc_C_et_al_Characterization_By_Atomic_Force_Microscopy_of_the_SOI_Layer.pdf	266316 data:960951bdcb3f80062b4fb1b8bd355eb3	no	4
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20	NPL Documents	Haisma_et_al_Silicon_on_Insulator-Wafer_Bonding.pdf	1279237 3c39415ab698224bd44b9596d2013fc88- a0e/	no	18
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21	NPL Documents	Hamaguchi_et_al_Device_Layer_Transfer_Technique.pdf	157984 e626f17472e9eb1c245cd8d154a678b05c- a0e/	no	3
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22	NPL Documents	Hamaguchi_et_al_Novel_LSI-SOI_Wafer.pdf	308961 b67919285b88c16a919579a13097a19- a0e/	no	4
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23	NPL Documents	Henttinen_et_al-Mechanically_Induced_Si_Layer.pdf	248942 004c90998ae2421b8496d1752ad5d294- a0e/	no	3
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24	NPL Documents	Hulett_DM_et_al_Ion_Nitriding_and_Ion_Impantation.pdf	228302 894673d4381b792e6d984eb3549a6d13- a0e/	no	4
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25	NPL Documents	IBM_Technical_Disclosure_Bulletin-Isolation_By_Inert_Ion_Implantation.pdf	31620 6441e02ff6f6aefc329eab1a2a6c60- a0e/	no	1
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26	NPL Documents	IBM-Tech-Disclosure-SOI-Interposer.PDF	135377 a0b476fb624620469a90f173be17b0264- a0e/	no	5
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27	NPL Documents	Jap-OA-Dated-10-25-07-2002-581572.pdf	209378 a150ec56186e19402f4064c2c95eef- a0e/	no	5
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28	NPL Documents	Jaussaud_C_et_al-Microstructure_of_Silicon_Implanted_With_High_Dose_Oxygen_Ions.pdf	393224 8ef1ac0b610d79ff0de6338055405c1fe- a0e/	no	3
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29	NPL Documents	Johnson-High_Fluence_Deuteron_Bombardment_of_Silicon.pdf	837642 463806ca21720f7ef3897a2d522f0f0f6e47f	no	9
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30	NPL Documents	Jones_KS_et_al-A_Systematic_Analysis_of_Defects_in_Ion_Implanted_Silicon.pdf	2789593 c0f4ef3bb3d0a6ec5a95f03c64456fdcb0bb	no	35
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31	NPL Documents	Jones_et_al_Enhanced_elimination_of_implantation_damage_upon_exceeding_the_solid_solvability.pdf	379786 d16f99fb468495a9c6a895ca209f187cf005	no	4
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32	NPL Documents	Kamada_et_al-Observation_of_Blistering_and_Amorphization_on_Germanium_Surface_After_keV.pdf	519461 b1ffecfb5e10bd48010fbfb6c6c16f114d3ef	no	6
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33	NPL Documents	Klem_Characteristics_of_Lift.pdf	393669 10a598e998186d788e8fb0f0aa1c1b1943f7c900	no	6
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34	NPL Documents	Komarov_et_al-Crystallographic_Nature_and_Formation_Mechanisms_of_Highly_Irregular_Structure.pdf	687131 9b8ec6d492ec0d5e491fb92d3196cda9584f6e	no	9
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35	NPL Documents	Kucheyev_et_al-Ion_Implantation_Into_GaN.pdf	3044381 d115f5ca16680254137cb8e0d94964126f98073	no	58
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36	NPL Documents	Laporte-A-et-al-Charged-Defects-at-the-Interface.pdf	1355175 4674164900e18a14d9975d96fbffbb6b39de5e	no	5
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37	NPL Documents	Li_J_Novel_Semiconductor_Substrate_Formed_By.pdf	51901 9e1e0130c4acc2f60d0a7ab3523301e3ec2d558	no	2
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38	NPL Documents	Ligeon_E-Hydrogen_Implantation_in_Silicon_Between_1-5_and_60_KeV.pdf	820674 2/8/11 10:12:13 5441616472086134592 cobs1	no	9
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39	NPL Documents	Liu_et_al-Ion_Implantation_in_GaN_at_Liquid-Nitrogen_Temperature.pdf	461874 e085050460202/15a056166507c19ec bb480	no	6
Warnings:					
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40	NPL Documents	Lu_X-SOI-Material-Technology-Using-Plasma_1.PDF	239638 104/11 10:05:57 25/10/2013 98547	no	2
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41	NPL Documents	Maleville-et-al-Physical-Phenomena-Involved_1.PDF	843600 4a6d6e5c12447e6aef491917ca24916d9 0244	no	18
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42	NPL Documents	Maleville_C_Wafer_Bonding_and_High-Implantation.pdf	266110 47d856a96b27cf0d7ab03c57423d5(bba) 3b53	no	6
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43	NPL Documents	Manuaba_A-Comparative_Study_on_Fe_Ni_Cr_P_Metallic_Glass_and_Its_Polycrystalline_Modification.pdf	1160732 499a4c111b0a0894d5975c840c991a4 8b65	no	11
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44	NPL Documents	Matsuda_et_al_Large_Diameter_Ion_Beam_Implantation_System.pdf	129012 607a95c5000c1220b8c5f6cc23b1c01b972c 2e2	no	3
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45	NPL Documents	Matsuo_et_al_Abnormal_solid_solution_and_activation_behavior_in_GA-implanted_Si100.pdf	207625 9945d4f3be17de7b9795e04ec8f8144 0ff7	no	3
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46	NPL Documents	Mishima_Y_and_T_Yagishita_Investigation_Of_The_Bubble_Formation.pdf	165000 6b7c6f1210be721abb64b19fb3b3265f 862	no	3
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47	NPL Documents	Miyagawa_S_et_al-Helium_Reemission_During_Implantation_of_Silicon_Carbide.pdf	375866 e0b902866e810478d3c2a9e7c5874d5488f49	no	5
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48	NPL Documents	Miyagawa_S_et_al-Surface_Structures_of_Silicon_Carbide_Irradiated_With_Helium_Ions.pdf	774178 e7d833542d4048c7f5c657379b161857947ed8d	no	9
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49	NPL Documents	Monemar_B-Shallow_Impurities_in_Semiconductors.pdf	485747 add1112-5d88b922-4b6e17f0-993c95ef9	no	6
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50	NPL Documents	Moreau_Wayne_M_Semiconductor_Lithography_Principles.pdf	497940 94914d614512e7c742510a2569a6b2a5cd2	no	17
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51	NPL Documents	Moriceau_H_et_al_A_New_Characterization_Process_Used_To.pdf	303042 0:60d94d9402bd4d8b25e74961e0b62d2535700	no	6
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52	NPL Documents	Moriceau_H_et_al_Cleaning_and_Polishing_As_Kep_Steps.pdf	151493 0:836e0195b1e4950235a03b25f6a477a6eccc96	no	2
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55	NPL Documents	Munteanu-et-al-Detailed-Characteristics-of-Unibond-Material.pdf	186594 0:039c1acae59b631c0f2ac265134352348a52a	no	4
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56	NPL Documents	Myers_DR-The_Effects_of_Ion-Implantation_Damage_on_The_First_Order_Raman_Spectra.pdf	676976 58622ef63c3a0c981152980a03bf1b7e34d07c	no	7
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57	NPL Documents	Neethling_CE_et_al-Identification_of_Hydrogen_Plantelets_in_Proton_Bombardment_GaAs.pdf	436026 58622ef5d4806c6d19851482ad2b85770097	no	5
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58	NPL Documents	Nichols_C_et_al_Properties_of_Hydrogen_in_Crystalline_Silicon.pdf	740397 58622ef904ec2b51a08e180d2e0d18c3d7f8	no	4
Warnings:					
Information:					
Total Files Size (in bytes):				32502614	
<p>This Acknowledgement Receipt evidences receipt on the noted date by the USPTO of the indicated documents, characterized by the applicant, and including page counts, where applicable. It serves as evidence of receipt similar to a Post Card, as described in MPEP 503.</p> <p>New Applications Under 35 U.S.C. 111 If a new application is being filed and the application includes the necessary components for a filing date (see 37 CFR 1.53(b)-(d) and MPEP 506), a Filing Receipt (37 CFR 1.54) will be issued in due course and the date shown on this Acknowledgement Receipt will establish the filing date of the application.</p> <p>National Stage of an International Application under 35 U.S.C. 371 If a timely submission to enter the national stage of an international application is compliant with the conditions of 35 U.S.C. 371 and other applicable requirements a Form PCT/DO/EO/903 indicating acceptance of the application as a national stage submission under 35 U.S.C. 371 will be issued in addition to the Filing Receipt, in due course.</p> <p>New International Application Filed with the USPTO as a Receiving Office If a new international application is being filed and the international application includes the necessary components for an international filing date (see PCT Article 11 and MPEP 1810), a Notification of the International Application Number and of the International Filing Date (Form PCT/RO/105) will be issued in due course, subject to prescriptions concerning national security, and the date shown on this Acknowledgement Receipt will establish the international filing date of the application.</p>					